



## AMENDMENT AND RESPONSE TO OFFICE ACTION

TO: COMMISSIONER OF PATENTS AND TRADEMARKS

Washington, D. C. 20231

FROM: George O. Saile (Reg. No. 19,572)

20 McIntosh Drive

Poughkeepsie, NY 12603

**DATE:** 16 July 2001

**REF:** APPLICANT : Chiang et al.

SERIAL NO. : 09/325,951

ART UNIT : 2812 FILING DATE : 06/04/99 ATT'Y NO. : TSMC 98-262

EXAMINER : R. Pompey

TITLE : Method for Forming High Purity Silicon Oxide Field

Oxide Isolation Region

Sir:

In response to an office action mailed on 22 May 2001, please consider the following amendments and remarks pertaining to the above referenced application.

## CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class mail in an envelope addressed to the Commissioner of Patents and Trademarks, Washington, D. C. 20231 on JO July 2001

zlal Signatiu

Date